

DMG7401SFG

P-CHANNEL ENHANCEMENT MODE MOSFET PowerDI3333-8

Product Summary

BV _{DSS}	R _{DS(ON)} max	I _D max T _A = +25°C
-30V	13mΩ @ V _{GS} = -10V	-9.8A
	$25m\Omega @ V_{GS} = -4.5V$	-7.0A

Description

This MOSFET is designed to minimize the on-state resistance $(R_{DS(ON)})$ and yet maintain superior switching performance, making it ideal for high efficiency power management applications.

Applications

- Backlighting
- Power Management Functions
- DC-DC Converters

Features and Benefits

- Low R_{DS(ON)} Ensures on state losses are minimized
- Small form factor thermally efficient package enables higher density end products
- Occupies just 33% of the Board Area Occupied by SO-8 Enabling Smaller End Product
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability
- An Automotive-Compliant Part is Available Under Separate Datasheet (DMG7401SFGQ)

Mechanical Data

- Case: PowerDI3333-8
- Case Material: Molded Plastic, "Green" Molding Compound.
 UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Connections Indicator: See Diagram
- Terminals: Finish Matte Tin Annealed over Copper Leadframe.
 Solderable per MIL-STD-202, Method 208 3
- Weight: 0.0174 grams (Approximate)



Ordering Information (Note 4)

		1
Part Number	Case	Packaging
DMG7401SFG-7	PowerDI3333-8	2000/Tape & Reel
DMG7401SFG-13	PowerDI3333-8	3000/Tape & Reel

Notes: 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.

2. See http://www.diodes.com/quality/lead_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.

3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.

4. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/.

Marking Information



G75 = Product Marking Code YYWW = Date Code Marking YY = Last Two Digits of Year (ex: 17 for 2017) WW = Week Code (01 to 53)

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Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic Drain-Source Voltage Gate-Source Voltage			Value	Unit V V
			-30	
			±25	
Steady State	T _A = +25°C T _A = +70°C	ID	-9.8 -7.7	А
t<10s	$T_A = +25^{\circ}C$ $T_A = +70^{\circ}C$ I_D		-13.5 -10.8	А
Maximum Continuous Body Diode Forward Current (Note 5)			-3.0	А
Pulsed Drain Current (10µs Pulse, Duty Cycle = 1%)			-80	А
Avalanche Current (Notes 7 & 8)			-14	А
Repetitive Avalanche Energy (Notes 7 & 8) L = 1mH			104	mJ
	State t<10s		State $T_A = +70^{\circ}C$ IDt<10s	$\begin{tabular}{ c c c c c c c c c c c c c c c c c c c$

Thermal Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic		Symbol	Value	Unit	
Total Power Dissipation (Note 5)	T _A = +25°C	Pn	0.94	W	
Total Power Dissipation (Note 5)	T _A = +70°C	PD	0.6	vv	
Thermal Resistance, Junction to Ambient (Note 5)	Steady State	P	137	°C/W	
Thermal Resistance, Junction to Ambient (Note 5)	t<10s	Reja	82	°C/W	
Total Power Dissipation (Note 6)	T _A = +25°C	Pn	2.2	W	
Total Fower Dissipation (Note 0)	T _A = +70°C	FD	1.3	vv	
Thermal Resistance, Junction to Ambient (Note 6)	Steady State	Desi	60	°C/W	
Thermal Resistance, Sunction to Ambient (Note 0)	t<10s	R _{0JA}	36	°C/W	
Thermal Resistance, Junction to Case (Note 6)		R _{θJC}	3,0	°C/W	
Operating and Storage Temperature Range		T _J , T _{STG}	-55 to +150	°C	

Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition	
OFF CHARACTERISTICS (Note 8)	_ Oynibor	INITI	Тур	IVIAN	Unit	Test condition	
Drain-Source Breakdown Voltage	BV _{DSS}	-30		_	V	$V_{GS} = 0V, I_{D} = -250\mu A$	
Zero Gate Voltage Drain Current	IDSS	_		-1	μA	$V_{DS} = -30V, V_{GS} = 0V$	
Gate-Source Leakage	I _{GSS}		_	±10	μA	$V_{GS} = \pm 20V, V_{DS} = 0V$	
ON CHARACTERISTICS (Note 8)						· · · ·	
Gate Threshold Voltage	V _{GS(TH)}	-1.7		-3.0	V	$V_{DS} = V_{GS}, I_{D} = -250 \mu A$	
			9	11	mΩ	V _{GS} = -20V, I _D = -12A	
Static Drain-Source On-Resistance	R _{DS(ON)}	-	10	13		$V_{GS} = -10V, I_D = -9A$	
			17	25		$V_{GS} = -4.5V, I_{D} = -5A$	
Forward Transfer Admittance	Y _{fs}	—	21	—	S	$V_{DS} = -5V, I_D = -10A$	
DYNAMIC CHARACTERISTICS (Note 9)							
Input Capacitance	Ciss	_	2246	2987	pF	V _{DS} = -15V, V _{GS} = 0V, f = 1.0MHz	
Output Capacitance	Coss		352	468	pF		
Reverse Transfer Capacitance	C _{rss}		294	391	рF		
Gate Resistance	Rg		5.1	10	Ω	$V_{DS} = 0V, V_{GS} = 0V, f = 1.0MHz$	
Total Gate Charge (V _{GS} = -4.5V)	Qg		20.5	30	nC		
Total Gate Charge (V _{GS} = -10V)	Qg		41	58	nC		
Gate-Source Charge	Q _{gs}	—	7.6	—	nC	$V_{DS} = -15V, I_D = -12A$	
Gate-Drain Charge	Q _{gd}	—	8.0	_	nC	7	
Turn-On Delay Time	t _{D(ON)}	—	11.3	23	ns		
Turn-On Rise Time	t _R	—	15.4	31	ns	V _{DD} = -15V, V _{GS} = -10V,	
Turn-Off Delay Time	t _{D(OFF)}	—	38.0	61	ns	$R_{L} = 1.25\Omega, R_{G} = 3\Omega$	
Turn-Off Fall Time	t _F	—	22.0	38	ns		
BODY DIODE CHARACTERISTICS	·					•	
Diode Forward Voltage	V _{SD}	—	-0.7	-1.0	V	$V_{GS} = 0V, I_{S} = -1A$	
Reverse Recovery Time (Note 9)	t _{RR}		20	31	ns		
Reverse Recovery Charge (Note 9)	Q _{RR}	—	9.5	18	nC	I _S = -9.5A, dl/dt = 100A/µs	

 Device mounted on FR-4 substrate PC board, 2oz copper, with minimum recommended pad layout.
 Device mounted on FR-4 substrate PC board, 2oz copper, with 1inch square copper plate. Notes:

7. I_{AR} and E_{AR} ratings are based on low frequency and duty cycles to keep $T_J = +25^{\circ}C$. 8. Short duration pulse test used to minimize self-heating effect.

9. Guaranteed by design. Not subject to product testing.



NOT RECOMMENDED FOR NEW DESIGN USE <u>DMP3018SFV</u>

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PowerDI3333-8

Package Outline Dimensions

Please see http://www.diodes.com/package-outlines.html for the latest version.



Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.



Dimensions	Value (in mm)
С	0.650
Х	0.420
X1	0.420
X2	0.230
X3	2.370
Y	0.700
Y1	1.850
Y2	2.250
Y3	3.700
Y4	0.540



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